

Silicon NPN Power Transistors

2SC2682

DESCRIPTION

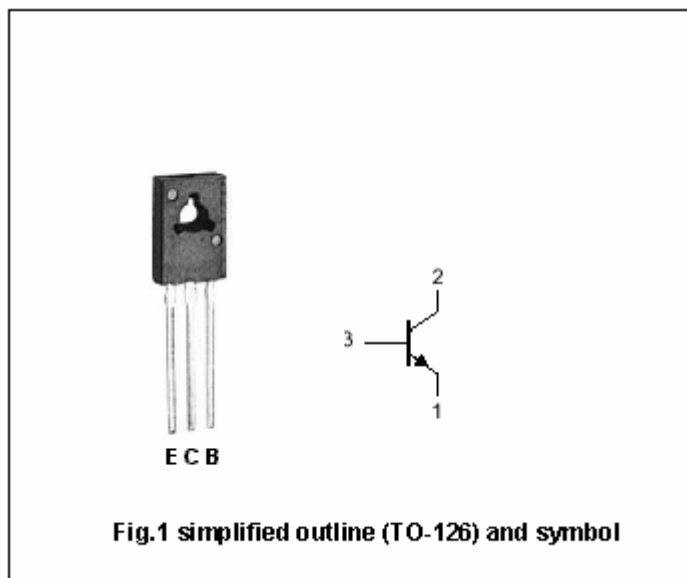
- With TO-126 package
- Complement to type 2SA1142

APPLICATIONS

- Audio frequency power amplifier; high frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	180	V
V_{CEO}	Collector-emitter voltage	Open base	180	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.1	A
P_C	Collector power dissipation	$T_a=25$	1.2	W
		$T_C=25$	10	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

 $T_j=25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=50mA$; $I_B=5mA$		0.12	0.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=50mA$; $I_B=5mA$		0.8	1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=180V$; $I_E=0$			1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=3V$; $I_C=0$			1	μA
h_{FE-1}	DC current gain	$I_C=1mA$; $V_{CE}=5V$	90	190		
h_{FE-2}	DC current gain	$I_C=10mA$; $V_{CE}=5V$	100	200	320	
f_T	Transition frequency	$I_C=20mA$; $V_{CE}=10V$		200		MHz
C_{ob}	Output capacitance	$I_E=0$; $V_{CB}=10V$; $f=1MHz$		3.2		pF

◆ h_{FE-2} Classifications

Q	P
100-200	160-320

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PACKAGE OUTLINE

